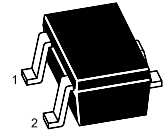
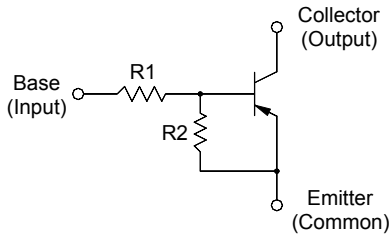


MMDTA124W

PNP Silicon Epitaxial Planar Digital Transistor



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Resistance Values

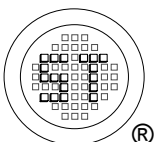
Type	R1 (KΩ)	R2 (KΩ)
MMDTA124W	22	22

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CB0}	50	V
Collector Emitter Voltage	-V _{CEO}	50	V
Emitter Base Voltage	-V _{EBO}	10	V
Input Voltage	V _I	- 40 to + 10	V
Collector Current	-I _C	100	mA
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at -V _{CE} = 5 V, -I _C = 5 mA	h _{FE}	60	-	-	-
Collector Base Cutoff Current at -V _{CB} = 50 V	-I _{CB0}	-	-	100	nA
Collector Emitter Cutoff Current at -V _{CE} = 30 V	-I _{CEO}	-	-	1	μA
Emitter Base Cutoff Current at -V _{EB} = 5 V	-I _{EBO}	-	-	180	μA
Collector Emitter Saturation Voltage at -I _C = 10 mA, -I _B = 0.5 mA	-V _{CEsat}	-	-	0.15	V
Input Off Voltage at -V _{CE} = 5 V, -I _C = 100 μA	-V _{I(off)}	-	-	0.8	V
Input On Voltage at -V _{CE} = 0.3 V, -I _C = 5 mA	-V _{I(on)}	2.5	-	-	V
Input Resistance	R1	15.4	22	28.6	KΩ
Resistance Ratio	R2/R1	0.8	1	1.2	-



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